

High-Performance Pin Driver

Features

- Clocking Speeds up to 40MHz
- 15ns tr/tf at 2000pF C_{LOAD}
- 0.5ns Rise and Fall Times Mismatch
- 0.5ns T_{ON}-T_{OFF} Prop Delay Mismatch
- 3.5pF Typical Input Capacitance
- 3.5A Peak Drive
- Low on Resistance of 3.5Ω
- High Capacitive Drive Capability
- Operates from 4.5V up to 18V

Applications

- ATE/Burn-in Testers
- Level Shifting
- IGBT Drivers
- CCD Drivers

Ordering Information

Part No.	Package	Tape & Reel	Outline #
EL7155CN	PDIP-8	-	MDP0031
EL7155CS	SO-8		MDP0027
EL7155CS-T7	SO-8	7 in	MDP0027
EL7155CS-T13	SO-8	13in	MDP0027

General Description

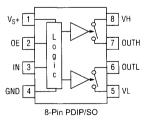
The EL7155C high-performance pin driver with tri-state is suited to many ATE and level-shifting applications. The 3.5A peak drive capability makes this part an excellent choice when driving high capacitance loads.

Output pins OUTH and OUTL are connected to input pins VH and VL respectively, depending on the status of the IN pin. One of the output pins is always in tri-state, except when the OE pin is active low, in which case both outputs are in tri-state mode. The isolation of the output FETs from the power supplies enables VH and VL to be set independently, enabling level-shifting to be implemented.

This pin driver has improved performance over existing pin drivers. It is specifically designed to operate at voltages down to 0V across the switch elements while maintaining good speed and on-resistance characteristics.

Available in the 8-Pin SO and 8-Pin PDIP packages, the EL7155C is specified for operation over the -40°C to +85°C temperature range.

Pin Layout Diagram



High-Performance Pin Driver

Absolute Maximum Ratings (T_A = 25°C)

Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Supply Voltage (V_{S+} to VL) +18V

Input Voltage VL -0.3V, VL₊ +0.3V

Continuous Output Current 200mA

Storage Temperature Range -65°C to +150°C

Ambient operating Temperature -40°C to +85°C

Operating Junction Temperature 125°C

Power Dissipation see curves

Maximum ESD 2kV

Important Note:

All parameters having Min/Max specifications are guaranteed. Typ values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore: $T_1 = T_C = T_A$

Electrical Characteristics

 V_{S+} = +15V, VH = +15V, VL = 0V, T_A = 25°C, unless otherwise specified.

Parameter	Description	Condition	Min	Тур	Max	Unit
Input					•	
V _{IH}	Logic '1' Input Voltage		2.4			v
I _{IH}	Logic '1' Input Current	$V_{IH} = V_S +$		0.1	10	μА
V_{IL}	Logic '0' Input Voltage				0.8	v
I _{IL}	Logic '0' Input Current	$V_{IL} = 0V$		0.1	10	μΑ
C _{IN}	Input Capacitance			3.5		pF
R _{IN}	Input Resistance			50		МΩ
Output			4.			
R _{OVH}	ON Resistance VH to OUTH	I _{OUT} = -200mA		2.7	4.5	Ω
R _{OVL}	ON Resistance VL to OUTL	$I_{OUT} = +200 \text{mA}$		3.5	5.5	Ω
I _{OUT}	Output Leakage Current	$OE = 0V$, $OUTH = VL$, $OUTL = V_S +$		0.1	10	μА
I _{PK}	Peak Output Current	Source		3.5		A
	(linear resistive operation)	Sink		3.5		A
I_{DC}	Continuous Output Current	Source/Sink	200			mA
Power Supply	y					
I _S	Power Supply Current	Inputs = V _{S+}		1.3	3	mA
I _{VH}	Off Leakage at VH	VH = 0V		4	10	μА
Switching Ch	aracteristics					
t _R	Rise Time	C _L =2000pF		14.5		ns
t _F	Fall Time	C _L = 2000pF		15		ns
t _{RFdelta}	t _R , t _F Mismatch	C _L = 2000pF		0.5		ns
t _{D-1}	Turn-Off Delay Time	C _L = 2000pF		9.5		ns
t _{D-2}	Turn-On Delay Time	$C_L = 2000 pF$		10		ns
t _{Ddelta}	t _{D-1} -t _{D-2} Mismatch	C _L = 2000pF		0.5		ns
t _{D-3}	Tri-State Delay Enable			10		ns
t _{D-4}	Tri-State Delay Disable			10		ns

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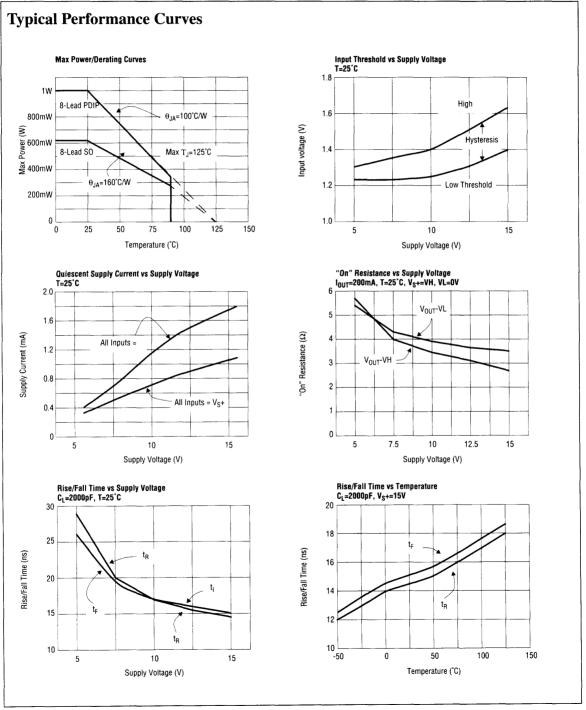
High-Performance Pin Driver

Electrical Characteristics

 V_S + = +5V, VH = +5V, VL = -5V, T_A = 25°C, unless otherwise specified.

Parameter	Description	Condition	Min	Тур	Max	Unit
Input					<u> </u>	<u> </u>
V _{IH}	Logic '1' Input Voltage		2.0			V
I _{IH}	Logic '1' Input Current	$V_{IH} = V_S +$		0.1	10	μΑ
V _{IL}	Logic '0' Input Voltage				0.8	V
I _{IL}	Logic '0' Input Current	$V_{IL} = 0V$		0.1	10	μΑ
C _{IN}	Input Capacitance			3.5		pF
R _{IN}	Input Resistance			50		ΜΩ
Output						
R _{OVH}	ON Resistance VH to OUTH	I _{OUT} = -200mA		3.4	5	Ω
R _{OVL}	ON Resistance VL to OUTL	$l_{OUT} = +200 \text{mA}$		4	6	Ω
I _{OUT}	Output Leakage Current	$OE = 0V$, $OUTH = VL$, $OUTL = V_S +$		0.1	10	μА
I _{PK}	Peak Output Current	Source		3.5		A
	(linear resistive operation)	Sink		3.5		A
I _{DC}	Continuous Output Current	Source/Sink	200			mA
Power Supply	7					
I _S	Power Supply Current	Inputs = V _S +		1	2.5	mA
I _{VH}	Off Leakage at VH	VH = 0V		4	10	μΑ
Switching Ch	aracteristics					
t _R	Rise Time	C _L =2000pF		17		ns
t _F	Fall Time	$C_L = 2000 pF$		17		ns
t _{RFdelta}	t _R , t _F Mismatch	$C_L = 2000 pF$		0		ns
t _{D-1}	Turn-Off Delay Time	$C_{L} = 2000 \text{pF}$		11.5		ns
t _{D-2}	Turn-On Delay Time	$C_{L} = 2000 pF$		12		ns
t _{Ddelta}	t _{D-1} -t _{D-2} Mismatch	$C_{L} = 2000 pF$		0.5		ns
t _{D-3}	Tri-State Delay Enable			11		ns
t _{D-4}	Tri-State Delay Disable			11		ns

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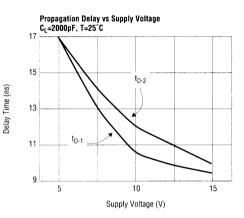


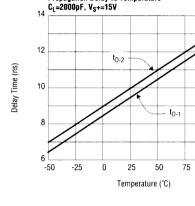
100

125

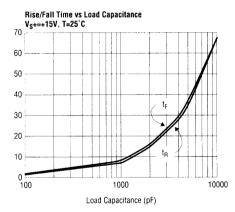
MOSFET Drivers & Comparators

Typical Performance Curves (cont.)

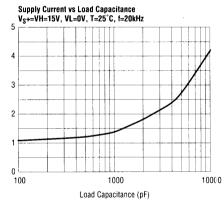


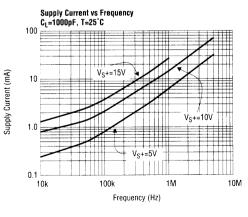


Propagation Delay vs Temperature



Rise/Fall Time (ns)





Supply Current (mA)

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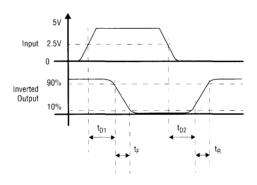
Truth Table

OE	IN	VH to OUTH	OUTL to VS.
0	0	Open	Open
0	1	Open	Open
1	0	Closed	Open
1	1	Open	Closed

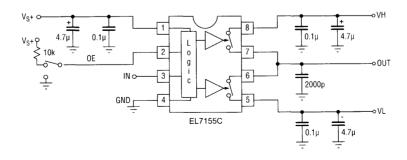
Operating Voltage Range

PIN	MIN	MAX
GND - VL	-5	0
V _S + - VL	5	18
VH - VL	0	18
V _S + - VH	0	18
V _S + - GND	5	18

Timing Diagrams



Standard Test Configuration

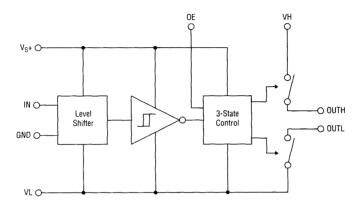


Pin Descriptions

3 4	V _S + OE IN GND	Positive Supply Voltage Output Enable	INPUT O VS+0 VLO Circuit 1
3	IN		INPUT O VLO
		Input	6 6: 11
4	GND	, ·	Same as Circuit 1
		Ground	
5	VL	Negative Supply Voltage	
6	OUTL	Lower Switch Output	OUIL Circuit 2
7	OUTH	Upper Switch Output	VL VL VL OVS+ Circuit 3

High-Performance Pin Driver

Block Diagram



Application Information

Product Description

The EL7155C is a high performance 40MHz pin driver. It contains two analog switches connecting VH to OUTH and VL to OUTL. Depending on the value of the IN pin, one of the two switches will be closed and the other switch open. An output enable (OE) is also supplied which opens both switches simultaneously.

Due to the topology of the EL7155C, VL should always be connected to a voltage equal to, or lower than GND. VH can be connected to any voltage between VL and the positive supply, V_S+ .

The EL7155C is available in both the 8-pin SO and the 8-pin PDIP packages. The relevant package should be chosen depending on the calculated power dissipation.

Supply Voltage Range and Input Compatibility

The EL7155C is designed for operation on supplies from 5V to 15V (4.5V to 18V maximum). The table on page 6 shows the specifications for the relationship between the V_{S+} , VH, VL, and GND pins.

All input pins are compatible with both 3V and 5V CMOS signals. With a positive supply (V_S+) of 5V, the EL7155C is also compatible with TTL inputs.

Power Supply Bypassing

When using the EL7155C, it is very important to use adequate power supply bypassing. The high switching currents developed by the EL7155C necessitate the use of a bypass capacitor between the V_S+ and GND pins. It

is recommended that a $2.2\mu F$ tantalum capacitor be used in parallel with a $0.1\mu F$ low-inductance ceramic MLC capacitor. These should be placed as close to the supply pins as possible. It is also recommended that the VH and VL pins have some level of bypassing, especially if the EL7155C is driving highly capacitive loads.

Power Dissipation Calculation

When switching at high speeds, or driving heavy loads, the EL7155C drive capability is limited by the rise in die temperature brought about by internal power dissipation. For reliable operation die temperature must be kept below T_{jmax} (125°C). It is necessary to calculate the power dissipation for a given application prior to selecting the package type.

Power dissipation may be calculated:

$$PD = (V_S \times I_S) + (C_{INT} \times V_S^2 \times f) + (C_L \times V_{OUT}^2 \times f)$$

Where:

- V_S is the total power supply to the EL7155C (from V_S + to GND),
- Vout is the swing on the output (VH VL),
- C_L is the load capacitance,
- CINT is the internal load capacitance (50pF max.),
- Is is the quiescent supply current (3mA max.) and
- f is frequency

Having obtained the application's power dissipation, a maximum package thermal coefficient may be determined, to maintain the internal die temperature below $T_{\rm imax}$:

$$\theta_{ja} = \frac{(T_{jmax} - T_{max})}{PD}$$

Where:

- T_{imax} is the maximum junction temperature (125°C),
- T_{max} is the maximum operating temperature,
- PD is the power dissipation calculated above,
- θ_{ia} thermal resistance on junction to ambient.

 θ_{ja} is 160°C/W for the SO8 package and 100°C/W for the PDIP8 package when using a standard JEDEC JESD51-3 single-layer test board. If T_{jmax} is greater than 125°C when calculated using the equation above, then one of the following actions must be taken:

- Reduce θ_{ja} the system by designing more heat-sinking into the PCB (as compared to the standard JEDEC JESD51-3)
- Use the PDIP8 instead of the SO8 package
- De-rate the application either by reducing the switching frequency, the capacitive load, or the maximum operating (ambient) temperature (T_{max})